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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/682,229	10/08/2003	Suguru Tabara	12844.0045US01	8128	
23552 75	90 09/30/2004		EXAMINER		
MERCHANT & GOULD PC P.O. BOX 2903			GOUDREAU, GEORGE A		
	S, MN 55402-0903		ART UNIT	PAPER NUMBER	
			1763		

DATE MAILED: 09/30/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
	10/682,229	TABARA, SUGURU	$\cap \langle \langle \rangle \rangle$
Office Action Summary	Examiner	Art Unit	
·	George A. Goudreau	1763	
The MAILING DATE of this communication Period for Reply	appears on the cover sheet wit	h the correspondence addre	ss
A SHORTENED STATUTORY PERIOD FOR RETHE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFI after SIX (6) MONTHS from the mailing date of this communication of the period for reply specified above is less than thirty (30) days, and the period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by stany reply received by the Office later than three months after the meanned patent term adjustment. See 37 CFR 1.704(b).	DN. R 1.136(a). In no event, however, may a re b. I reply within the statutory minimum of thirty riod will apply and will expire SIX (6) MONT atute. cause the application to become ABA	ply be timely filed (30) days will be considered timely. HS from the mailing date of this commo	unication.
Status		•	
1) Responsive to communication(s) filed on (10-8-03' to 1-7-04').		
	This action is non-final.		
3) Since this application is in condition for allo	wance except for formal matte	rs, prosecution as to the me	erits is
closed in accordance with the practice und	er Ex parte Quayle, 1935 C.D.	11, 453 O.G. 213.	Ì
Disposition of Claims			
4) Claim(s) 1-12 is/are pending in the applicat	ion		
4a) Of the above claim(s) is/are with			
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-9,11 and 12</u> is/are rejected.			
7)⊠ Claim(s) <u>10</u> is/are objected to.		•	
8) Claim(s) are subject to restriction an	d/or election requirement.		
Application Papers			
9)☐ The specification is objected to by the Exam	niner		
10) The drawing(s) filed on is/are: a) a		v the Examiner	
Applicant may not request that any objection to			- }
Replacement drawing sheet(s) including the con		, ,	.121(d).
11)☐ The oath or declaration is objected to by the			
Priority under 35 U.S.C. § 119			
 12) Acknowledgment is made of a claim for fore a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the p 	ents have been received. ents have been received in Ap _l	plication No	ae .
application from the International Bur	eau (PCT Rule 17.2(a)).		
* See the attached detailed Office action for a	list of the certified copies not re	eceived.	
Attachment(s)		GEORGE GOU PRIMARY EX	JOHEAU AMINER
) ⊠ Notice of References Cited (PTO-892)	4) 🔲 Interview Sur	mmary (PTO-413)	
Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/NPaper No(s)/Mail Date	Paper No(s)/I	nmary (P10-413) Mail Date rmal Patent Application (PT0-152))
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1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1-2, 6-7, 9, and 11-12 are rejected under 35 U.S.C. 102(b) as being anticipated by Shen et. al. (5,948,703).
 - Shen et. al. disclose a multi-step rie etching process for patterning a polysi gate on top of a SiO2 gate oxide layer which is comprised of the following steps:
 - -The top portion of the polysi layer is anisotropically rie etched using a plasma which is comprised of Cl2-He-O2-N2.; and
 - -The remaining portion of the polysi layer is anisotropically rie etched using a plasma, which is comprised of HBr-Cl2-He-O2.
 - This is discussed in columns 1-8. This is shown in figures 1-8.
- 3. Claims 1-3, 6-9, and 12 are rejected under 35 U.S.C. 102(b) as being anticipated by Mckee (5,804,088).
 - Mckee disclose a multi-step rie etching process for patterning a polysi gate on top of a SiO2 gate oxide layer which is comprised of the following steps:
 - -The top portion of the polysi layer is anisotropically rie etched using a plasma which is comprised of SF6-HBr in an ECR type plasma etcher.; and
 - -The remaining portion of the polysi layer is anisotropically rie etched using a plasma, which is comprised of HBr-Cl2-He-O2 in an ECR type plasma etcher. This is discussed in columns 1-8. This is shown in figures 1-9.

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4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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- 5. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 6. Claims 4-5, and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shen et. al. as applied in paragraph 2 above.
 - Shen et. al. as applied in paragraph 2 above fail to disclose the following aspects of applicant's claimed invention:
 - -the specific etch process parameters which are claimed by the applicant; and -the specific usage of a gate SiO2 layer of the specific thickness, which is claimed by the applicant

It would have been obvious to one skilled in the art to employ a gate oxide layer of the specific thickness, which is claimed by the applicant based upon the following. It would have been desirable to provide a gate oxide of sufficient thickness to provide

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adequate electrical insulation between the gate, and the wafer without forming an excessively thick gate oxide layer which would undesirably waste both precious processing time, and materials.

It would have been prima facie obvious to employ any of a variety of different etch process parameters in the rie etching process taught above including those which are specifically claimed by the applicant. These are all well known variables in the plasma etching art, which are known to effect both the rate and the quality of the plasma etching process. Further, the selection of particular values for these variables would not necessitate any undo experimentation, which would have been indicative of unexpected results.

Alternatively, it would have been obvious to one skilled in the art to employ the specific etch process parameters which are claimed by the applicant in the rie etching process which is taught above based upon In re Aller as cited below.

"Where the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F. 2d 454, 105 USPQ 233, 235 (CCPA).

Further, all of the specific process parameters which are claimed by the applicant are results effective variables whose values are known to effect both the rate, and the quality of the plasma etching process.

7. Claims 4-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mckee as applied in paragraph 3 above.

Mckee as applied in paragraph 3 above fail to disclose the following aspects of applicant's claimed invention:

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- -the specific etch process parameters, which are claimed by the applicant;
- -the specific usage of a gate SiO2 layer of the specific thickness which is claimed by the applicant; and
- -the specific usage of an ECR type plasma etching apparatus to conduct the etching process

It would have been obvious to one skilled in the art to employ a gate oxide layer of the specific thickness, which is claimed by the applicant based upon the following. It would have been desirable to provide a gate oxide of sufficient thickness to provide adequate electrical insulation between the gate, and the wafer without forming an excessively thick gate oxide layer which would undesirably waste both precious processing time, and materials.

It would have been prima facie obvious to employ any of a variety of different etch process parameters in the rie etching process taught above including those which are specifically claimed by the applicant. These are all well known variables in the plasma etching art, which are known to effect both the rate and the quality of the plasma etching process. Further, the selection of particular values for these variables would not necessitate any undo experimentation, which would have been indicative of unexpected results.

Alternatively, it would have been obvious to one skilled in the art to employ the specific etch process parameters which are claimed by the applicant in the rie etching process which is taught above based upon In re Aller as cited below.

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"Where the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F. 2d 454, 105 USPQ 233, 235 (CCPA).

Further, all of the specific process parameters which are claimed by the applicant are results effective variables whose values are known to effect both the rate, and the quality of the plasma etching process.

It would have been obvious to one skilled in the art to employ an ECR plasma etcher in the conduction of the plasma etching process taught above based upon the following. The usage of an ECR plasma etcher is conventional or at least well known in the plasma etching arts. (The examiner takes official notice in this regard.) Further, the specific usage of an ECR plasma etcher to conduct the etching process taught above simply represents the usage of an alternative, and at least equivalent means for conducting the plasma etching process taught above to the specific means which are taught above.

- 8. Claim 10 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 9. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

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10. Any inquiry concerning this communication should be directed to examiner

George A. Goudreau at telephone number (571)-272-1434.

George A. Goudreau Primary Examiner Art Unit 1763